

Semiconductor Memory Design and Testing QUESTION BANK

UNIT-1

- 1) Explain how Read Upset is addressed in SRAM Read operation with necessary diagram and condition.
- 2) Explain the Transistor sizing to be maintained so that the SRAM cell allows modification of the stored information.
- 3) What is the Significance of Butterfly curve? Explain it with Hold and Read state butterfly curves. Comment why stability is HIGH in hold state.
- 4) Explain the working of 6T SRAM and also draw the layout/ stick diagram for the
- 5) same.
- 6) Write a comparison between 4T, 6T and 7T SRAM Cells.
- 7) Why sense amplifier need to be isolated from bit lines? Explain the function of bit switch Isolation circuit.
- 8) What is metastable state of cross coupled Inverters? Explain how cross coupled Inverters work as Sense amplifier in SRAM.
- 9) Explain how Sense Amplifier Signal is being developed and latched with a neat waveform.
- 10) What is the function of pre-charge circuit? Explain the significance of equalizer transistor in 3 transistor pre-charge circuit.
- 11) Explain the working of 3 bit Static Decoder using NOR and what are the challenges of Decoder using NOR.
- 12) Explain the Hierarchical Decoders and it's advantage over decoder using NOR. Also write it's drawbacks.
- 13) Calculate Number of Transistors required to design 8:256 Decoder using
 - a. Single stage NAND Decoder
 - b. NAND gate Decoder using pre-decoder
- 14) Explain dynamic , 2 to 4 NAND and NOR decoder.

